

**10/588775**

**IAP11 Rec'd PCT/PTO 08 AUG 2006**

**PATENT APPLICATION**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re application of

Docket No: Q96219

Yasuhiro OKAMOTO, et al.

PCT/JP2005/002712

-filed February 21, 2005

Appln. No.: Not assigned yet

Confirmation No.: Not assigned yet

Group Art Unit: Not assigned yet

Filed: August 8, 2006

Examiner: Not assigned yet

For: FIELD EFFECT TRANSISTOR

**INFORMATION DISCLOSURE STATEMENT**  
**UNDER 37 C.F.R. §§ 1.97 and 1.98**

**MAIL STOP AMENDMENT**

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

1. Japanese Patent Application Publication No. 2000-100831, published April 7, 2000, along with English-Language Abstract;

2. Japanese Patent Application Publication No. 2001-308110, published November 2, 2001, along with English-Language Abstract;

3. Japanese Patent Application Publication No. 2004-022773, published January 22, 2004, along with English-Language Abstract;

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U.S. Appln. to Yasuhiro OKAMOTO et al.

4. Japanese Patent Application Publication No. 2003-273130, published September 26, 2003, along with English-Language Abstract;

5. Japanese Patent Application Publication No. 07-321126, published December 8, 1995, along with English-Language Abstract;

6. Japanese Patent Application Publication No. 04-154171, published May 27, 1992, which corresponds with Japanese Patent No. 2744126, issued February 6, 1998;

7. Japanese Patent Application Publication No. 56-088364, published July 17, 1981, along with English-Language Abstract;

8. J. Li et al. "High Breakdown Voltage GaN HFET with field plate" Electronics Letters, February 1, 2001, Vol. 37 No. 3 p. 196-197.

Japanese Patent Application Publication No. 2005-19765, published January 20, 2005, which corresponds with U.S. Patent Application Publication No. 2005/0017357

One copy of each of the listed documents is submitted herewith.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

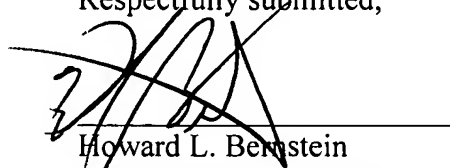
In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that reference 8, is cited within the specification beginning page 3, line 5. Applicants enclose herewith a copy of an International Search Report citing documents 1-5, indicating the degree of relevance found by the foreign patent office.

INFORMATION DISCLOSURE STATEMENT  
U.S. Appln. to Yasuhiro OKAMOTO et al.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

  
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WASHINGTON OFFICE

23373

CUSTOMER NUMBER

Date: August 8, 2006

Substitute for Form 1449 A & B/PTO  <b><u>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</u></b>  <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not assigned
				Confirmation Number	Not assigned yet
				Filing Date	August 8, 2006
				First Named Inventor	Yasuhiro OKAMOTO
				Art Unit	Not assigned yet
				Examiner Name	Not assigned yet
				Attorney Docket Number	Q96219
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US			
		US			
		US			
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		US			
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> <i>(if known)</i>			
		JP	2000-100831	A	04-07-2000		
		JP	2001-308110	A	11-02-2001		
		JP	2004-022773	A	01-22-2004		
		JP	2003-273130	A	09-26-2003		
		JP	07-321126	A	12-08-1995		
		JP	04-154171	A	05-27-1992		
		JP	56-088364	A	07-17-1981		
		JP	2744126	B	02-06-1998		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
		J. Li et al. "High Breakdown Voltage GaN HFET with field plate" Electronics Letters, February 1, 2001, Vol. 37 No. 3 p. 196-197.	

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.